

# 2SC3710

Silicon NPN Transistors



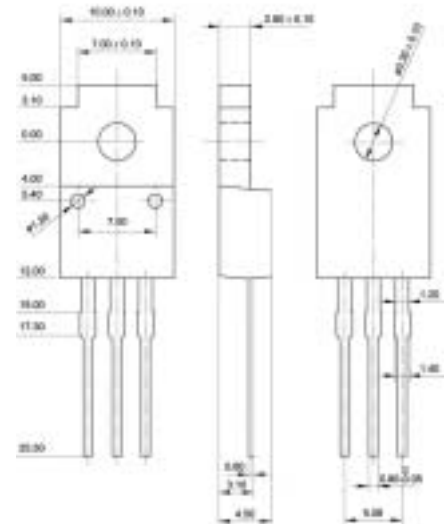
BCE

### ◆ Features

- . With TO-220Fa package
- . Complement to type 2SA1452
- . High current switching applications

### ◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CB0</sub>	Collector to base voltage	80	V
V <sub>CEO</sub>	Collector to emitter voltage	80	V
V <sub>EBO</sub>	Emitter to base voltage	6	V
I <sub>B</sub>	Base current	2	A
I <sub>C</sub>	Collector current	12	A
P <sub>C</sub>	Collector power dissipation	30	W
T <sub>j</sub>	Junction temperature	150	°C
T <sub>stg</sub>	Storage temperature	-55~150	°C



TO-220Fa

### ◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	Typ.	MAX	UNIT
I <sub>CB0</sub>	Collector cut-off current	V <sub>CB</sub> =80V; I <sub>E</sub> =0			10	uA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			10	uA
V <sub>CB0</sub>	Collector-base breakdown voltage					
V <sub>CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA; I <sub>B</sub> =0	80			V
V <sub>EBO</sub>	Emitter-base breakdown voltage					
V <sub>CE(sat-1)</sub>	Collector-emitter saturation voltages	I <sub>C</sub> =6A; I <sub>B</sub> =0.3A			0.4	V
V <sub>CE(sat-2)</sub>	Collector-emitter saturation voltages					
h <sub>FE-1</sub>	Forward current transfer ratio	I <sub>C</sub> =1A; V <sub>CE</sub> =1V	70		240	
h <sub>FE-2</sub>	Forward current transfer ratio	I <sub>C</sub> =6A; V <sub>CE</sub> =1V	40			
V <sub>BE(sat-1)</sub>	Base-emitter saturation voltages	I <sub>C</sub> =6A; I <sub>B</sub> =0.3A			1.2	V
V <sub>BE(sat-2)</sub>	Base-emitter saturation voltages					
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A; V <sub>CE</sub> =5V		80		MHz
C <sub>ob</sub>	Collector Out put Capacitance	V <sub>CB</sub> =10V; f=1MHz		220		pF

### ◆ h<sub>FE-1</sub> Classifications

O	Y
70-140	120-240